

ABSTRACT OF DISCLOSURE

A magnetic memory device includes a magneto-resistance effect element including a magnetic sensitive layer whose magnetization direction changes according to an external magnetic field; a write line to which a write current is supplied to apply an external magnetic field to the magnetic sensitive layer; and a write current drive circuit including a current direction control section for controlling the direction of the write current in the write line and a current amount control section for controlling the amount of the write current in the write line to a constant value.

[Selected drawing] FIG. 4